

DETAILED COURSE SYLLABUS (*TENTATIVE*)

The following comprises a **tentative** syllabus describing the material to be covered in this course. Material to be covered for each dated lecture is indicated along with the corresponding sections of the required textbooks, where S = Senturia's "Microsystem Design" (i.e., required text), K = Kovacs' "Micromachined Transducers Sourcebook" (i.e., supplementary text), and J = Jaeger's "Introduction to Microelectronic Fabrication" (i.e., supplementary text).

Date		Lec #	Material to be Covered	Reading Assignment
Aug.	23	1	Administrative Information, MEMS Roadmaps, Benefits of Miniaturization	S: §1.1-1.4
	28	2	Benefits of Scaling I: faster speed (transistors, micromechanical resonators)	
	*30	3	Benefits of Scaling II: lower power consumption (micro-ovens)	
Sept.	4	4	Benefits of Scaling III: higher sensitivity (gas sensors)	
	6	5	Fabrication Process Modules I: oxidation, film deposition, lithography	S: §3.1-3.2.3, §3.2.6, §3.3.1 J: §2.1, §2.3-2.5, §3.1-3.3, §3.6, §6.1-6.3
	11	6	Fabrication Process Modules II: etching, ion implantation, diffusion	S: §3.2.5, §3.3.4.1, §3.3.5-3.3.6 J: §2.2, §4.1-4.5, §5.1-5.5
	13	7	Surface Micromachining I: basic polysilicon process flow, release, sacrificial & structural material choices	S: §4.1-4.4 J: §11.4.1-11.4.2
	18	8	Surface Micromachining II: 2 nd order issues, stiction, residual stress, electroplating, 3D out-of-plane MEMS	S: §8.3, §13.2.3 J: §11.4.3-11.4.4
	20	9	Surface Micromachining III: MUMPS, design rules, Summit	Handout
	25	10	Bulk Micromachining: wet etch-based, dissolved wafer process, SOI MEMS, Scream, Hexsil MEMS, sealed cavity deep RIE	S: §3.3.4.2-3.3.4.3 J: §11.2-11.3, §11.6
	27	11	Mechanics of Materials for MEMS I: stress, strain, material properties, measurement & characterization of mechanical parameters	S: §8.1-8.2, §8.4
Oct.	2	12	Mechanics of Materials for MEMS II: quality factor, beam bending	S: §7.2.2, §9.1-9.3
	4	13	Mechanics of Materials for MEMS III: practical stress, beam combos, stressed folded flexures	
	9	14	Energy Methods I: virtual work, energy formulations, tapered beam example	S: §10.1-10.3
	11	15	Energy Methods II: clamped-clamped beam example, large deflection analysis, estimating resonance frequency	S: §10.5
	16	16	Equivalent Circuits I: dynamic mass, stiffness, and damping, example: free-free beam, lumped mass-spring-damper circuit	S: §10.5.2, Handout
	18	17	Equivalent Circuits II: electromechanical analogies, lossless transducers	S: §5.1-5.6, Handout
	23	18	Lossless Transducers I: capacitive transducers, charge control, voltage control, spring suspended C, parallel-plate capacitive transducer, pull-in, linearization	S: §6.1-6.4
	25		Midterm Exam	
	30	19	Lossless Transducers II: electrical stiffness, comb drive, levitation	Handouts
Nov.	1	20	Equivalent Circuits III: input modeling, force-to-velocity relationship & circuit, intro. to gyroscopes	S: §6.6, §19.1-19.2, §21.1-21.2
	6	21	Equivalent Circuits IV: output modeling, input-to-output transconductance, complete equivalent circuit	Handout
	8	22	Sensing Circuits I: ideal op amps, velocity sensing, position sensing	S: §14.9, §14.11.2
	13	23	Sensing Circuits II: differential position sensing, MEMS/transistor integration	S: §19.1-19.4 J: §7.7, §9.3, §11.7
	15	24	Sensing Circuits III: non-ideal op amps, begin noise	S: §14.10-14.11, S: Chpt. 15
	20	25	Sensor Resolution I: noise sources, noise calculation, min. detectable signal	S: §16.1, §16.3-16.6
	22		Thanksgiving—Holiday	
	27	26	Sensor Resolution II: noise calculation examples, gyro example	Handouts
	29	27	MEMS-Transistor Integration: mixed, MEMS-first, MEMS-last	Handouts
Dec.	4		Reading/Recitation/Review Day—No Lecture	
	6		Reading/Recitation/Review Day—No Lecture	
			Final Exam: Friday, Dec. 14, 7-10 p.m. (Exam Group 20)	

* The asterisks indicate days that I will not be in town. On these dates I will make appropriate arrangements for the lecture, which will probably entail doing and recording (for website posting) a make-up lecture at a specified time and location.